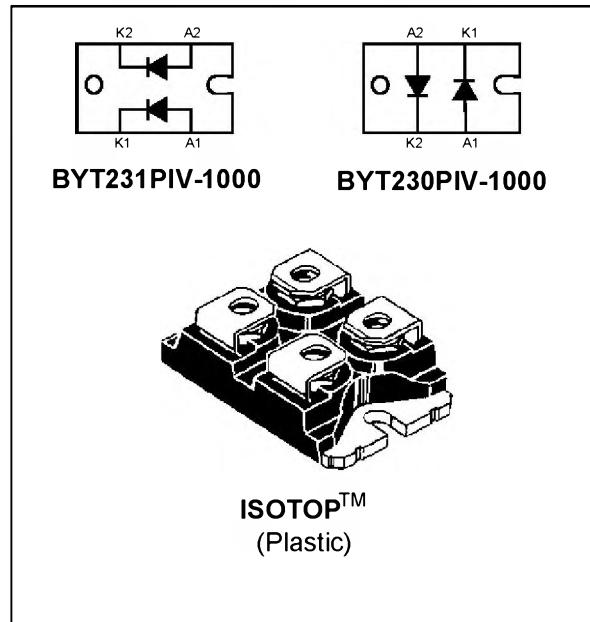


## FAST RECOVERY RECTIFIER DIODES

### FEATURES

- VERY LOW REVERSE RECOVERY TIME
- VERY LOW SWITCHING LOSSES
- LOW NOISE TURN-OFF SWITCHING
- INSULATED PACKAGE :
  - Insulating voltage = 2500 V<sub>RMS</sub>
  - Capacitance = 45 pF



### DESCRIPTION

Dual high voltage rectifiers suited for Switch Mode Power Supplies and other power converters.  
 The devices are packaged in ISOTOP.

### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter			Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage			1000	V
$I_{FRM}$	Repetitive peak forward current	$t_p \leq 10\mu s$		375	A
$I_{F(RMS)}$	RMS forward current		Per diode	70	A
$I_{F(AV)}$	Average forward current	$T_c=55^\circ C$ $\delta = 0.5$	Per diode	30	A
$I_{FSM}$	Surge non repetitive forward current	$t_p=10ms$ sinusoidal	Per diode	200	A
$T_{stg}$ $T_j$	Storage and junction temperature range			- 40 to + 150	°C
				- 40 to + 150	°C

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## BYT230PIV-1000 / BYT231PIV-1000

### THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
R <sub>th</sub> (j-c)	Junction to case	Per diode	1.5
		Total	0.8
R <sub>th</sub> (c)	Coupling	0.1	°C/W

When the diodes 1 and 2 are used simultaneously :  
 $\Delta T_j(\text{diode } 1) = P(\text{diode}) \times R_{th}(\text{Per diode}) + P(\text{diode } 2) \times R_{th}(c)$

### ELECTRICAL CHARACTERISTICS (Per diode)

#### STATIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
V <sub>F</sub> *	T <sub>j</sub> = 25°C	I <sub>F</sub> = 30 A			1.9	V
	T <sub>j</sub> = 100°C				1.8	
I <sub>R</sub> **	T <sub>j</sub> = 25°C	V <sub>R</sub> = V <sub>RRM</sub>			100	μA
	T <sub>j</sub> = 100°C				5	

Pulse test : \* tp = 380 μs, duty cycle < 2 %

\*\* tp = 5 ms, duty cycle < 2 %

### RECOVERY CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
trr	T <sub>j</sub> = 25°C	I <sub>F</sub> = 0.5A	I <sub>rr</sub> = 0.25A		70	ns
		I <sub>R</sub> = 1A			165	
		I <sub>F</sub> = 1A	dI <sub>F</sub> /dt = -15A/μs			
		V <sub>R</sub> = 30V				

### TURN-OFF SWITCHING CHARACTERISTICS (Without serie inductance)

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
t <sub>IRM</sub>	dI <sub>F</sub> /dt = -120A/μs	V <sub>CC</sub> = 200V L <sub>p</sub> ≤ 0.05μH see fig. 11	I <sub>F</sub> = 30A		200	ns
	dI <sub>F</sub> /dt = -240A/μs		T <sub>j</sub> = 100°C	120		
I <sub>RM</sub>	dI <sub>F</sub> /dt = -120A/μs				19.5	A
	dI <sub>F</sub> /dt = -240A/μs				22	

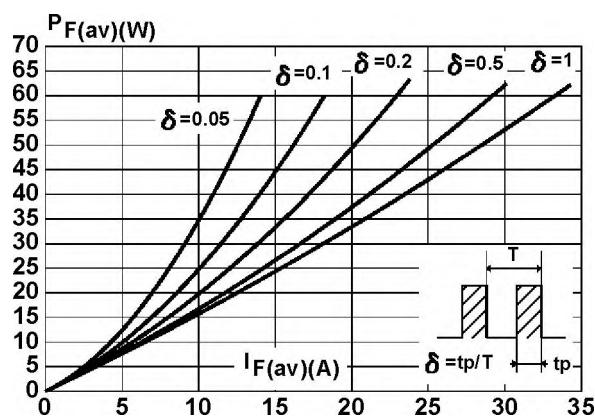
### TURN-OFF OVERVOLTAGE COEFFICIENT (With serie inductance)

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
C = $\frac{V_{RP}}{V_{CC}}$	T <sub>j</sub> = 100°C dI <sub>F</sub> /dt = -30A/μs	V <sub>CC</sub> = 200V L <sub>p</sub> = 5μH see fig.12	I <sub>F</sub> =I <sub>F(AV)</sub>		4.5	/

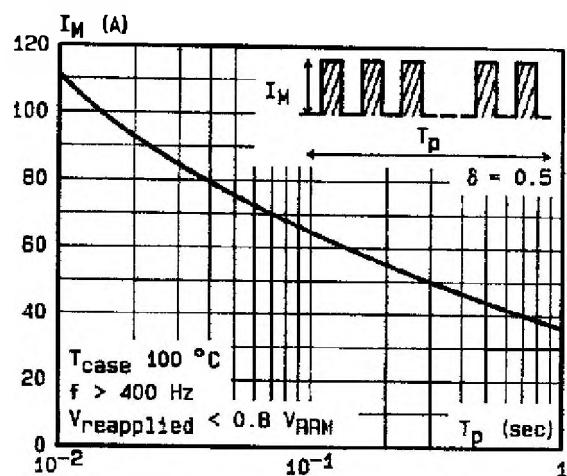
To evaluate the conduction losses use the following equation :

$$P = 1.47 \times I_{F(AV)} + 0.010 \times I_F^2 (\text{RMS})$$

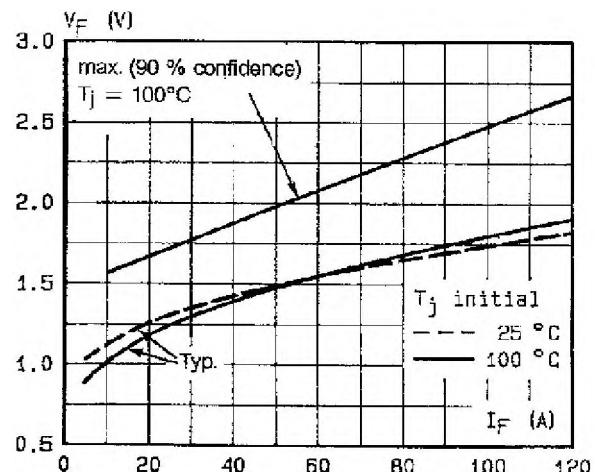
**Fig.1** : Low frequency power losses versus average current.



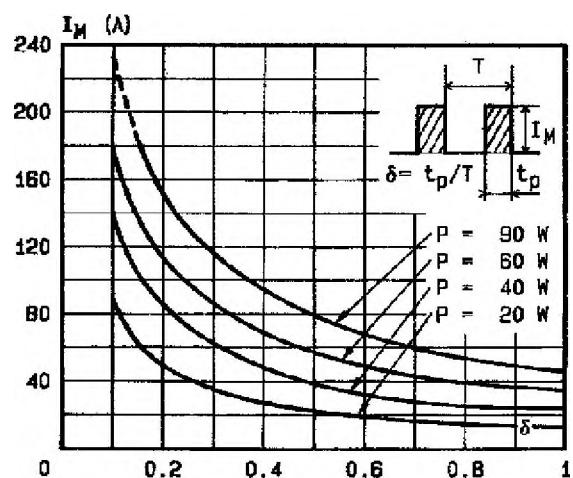
**Fig.3** : Non repetitive peak surge current versus overload duration.



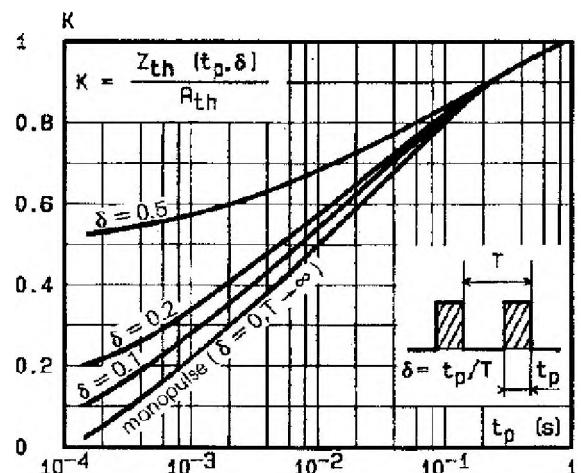
**Fig.5** : Voltage drop versus forward current.



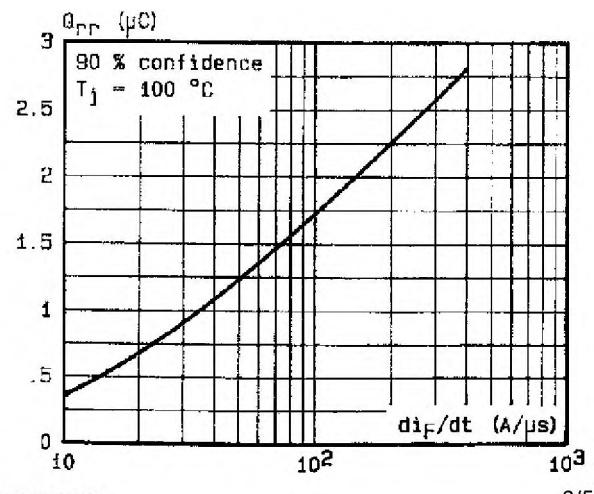
**Fig.2** : Peak current versus form factor.



**Fig.4** : Relative variation of thermal impedance junction to case versus pulse duration.



**Fig.6** : Recovery charge versus diF/dt.



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Fig.7 : Recovery time versus  $dI_F/dt$ .

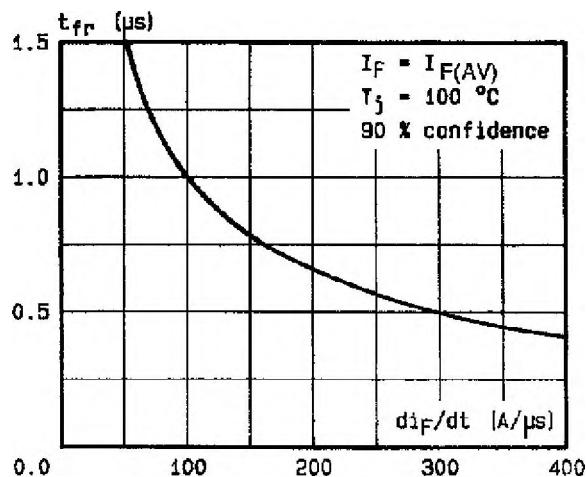


Fig.9 : Peak forward voltage versus  $dI_F/dt$ .

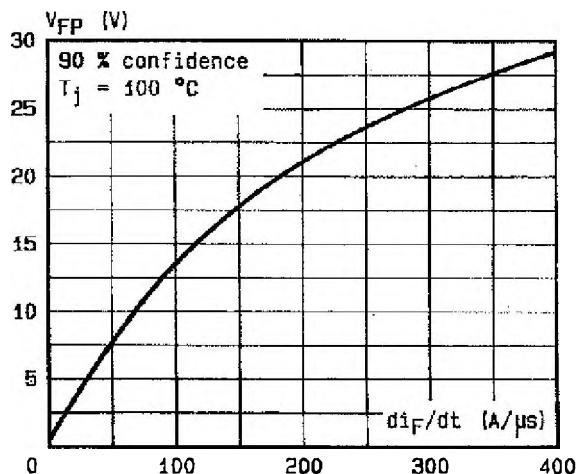
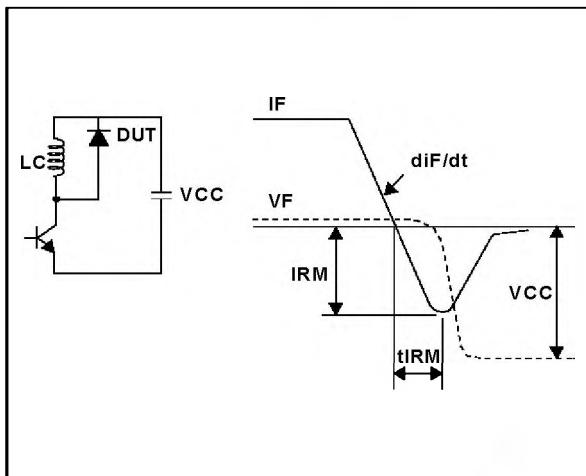


Fig.11 : TURN-OFF SWITCHING CHARACTERISTICS (Without serie inductance)



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Fig.8 : Peak reverse current versus  $dI_F/dt$ .

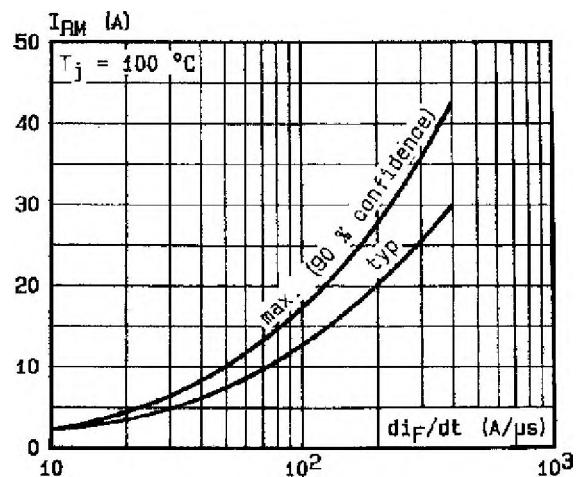


Fig.10 : Dynamic parameters versus junction temperature.

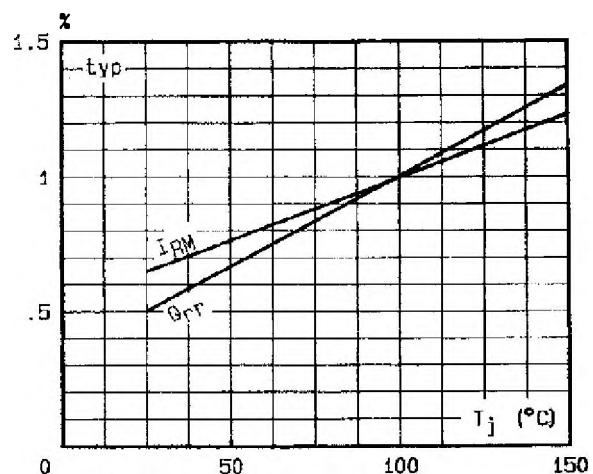
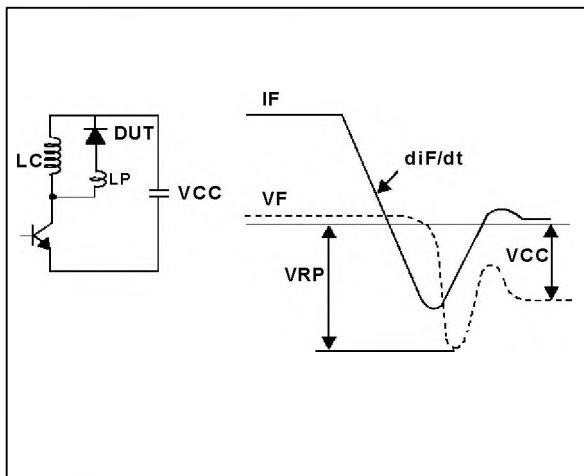
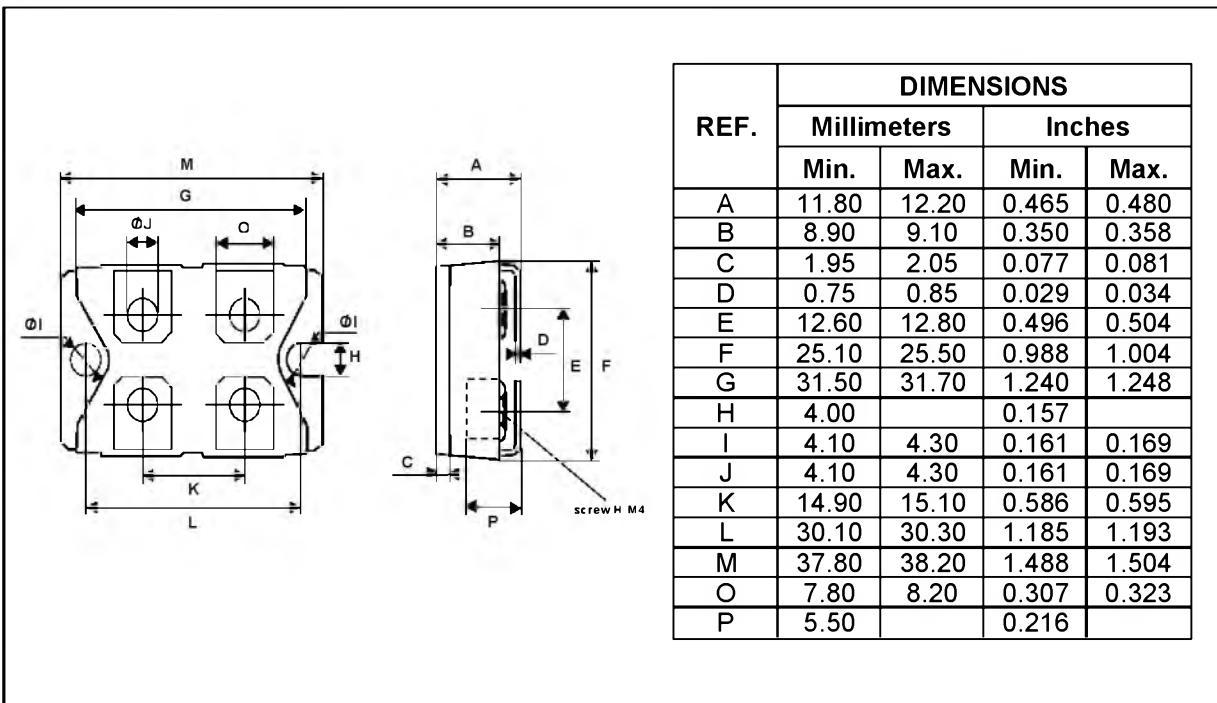


Fig.12 : TURN-OFF SWITCHING CHARACTERISTICS (With serie inductance)



**PACKAGE MECHANICAL DATA**  
 ISOTOP Screw version



REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	11.80	12.20	0.465	0.480
B	8.90	9.10	0.350	0.358
C	1.95	2.05	0.077	0.081
D	0.75	0.85	0.029	0.034
E	12.60	12.80	0.496	0.504
F	25.10	25.50	0.988	1.004
G	31.50	31.70	1.240	1.248
H	4.00		0.157	
I	4.10	4.30	0.161	0.169
J	4.10	4.30	0.161	0.169
K	14.90	15.10	0.586	0.595
L	30.10	30.30	1.185	1.193
M	37.80	38.20	1.488	1.504
O	7.80	8.20	0.307	0.323
P	5.50		0.216	

Cooling method : C

Marking : Type number

Weight : 28 g (without screws)

Electrical isolation : 2500V<sub>(RMS)</sub>

Capitance : &lt; 45 pF

Inductance : &lt; 5 nH

- Recommended torque value : 1.3 N.m (MAX 1.5 N.m) for the 6 x M4 screws. (2 x M4 screws recommended for mounting the package on the heatsink and the 4 screws given with the screw version).
- The screws supplied with the package are adapted for mounting on a board (or other types of terminals) with a thickness of 0.6 mm min and 2.2 mm max.

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